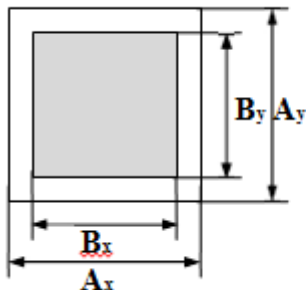




SM-24N

Chip TVS diode



Schematic and pinning diagram.

Mechanical date: $A_x=A_y=580\mu\text{m}$

$B_x=B_y=420\mu\text{m}$

Chip thickness: a) $138\pm 12\mu\text{m}$

b) $230\pm 20\mu\text{m}$

c) $470 \pm 20\mu\text{m}$

Scribe Line width - $60\mu\text{m}$.

Top Metal: Al metallization for wire bond

Back side - Cathode: a) Ti-Ni-Ag for soldering.

b) without metallization.

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	V_{RWM}	-	24,0	V
Peak Pulse Power	P_{pp}	$t_p=8/20\mu\text{s}$	300*	W
Peak Pulse Current	I_{pp}	$t_p=8/20\mu\text{s}$	5	A
Max.junction temperature	T_j	-	+125	°C

Characteristics ($T_j=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{BR}	Breakdown voltage	$I_R=1\text{mA}$	27,0	32,0	35,0	V
I_R	Reverse leakage current	$V_R=24.0\text{V}$			0,9	μA
V_{CL}	Clamping Voltage	$I_{pp}=1.0\text{A}, t_p=8/20\mu\text{s}$ $I_{pp}=5\text{A}, t_p=8/20\mu\text{s}$			42* 60*	V
C_j	Diode capacitance	$V_R=0\text{V}, f=1\text{MHz}$		60		pF

*For Device testing